DUAL-BRIDGE MOTOR CONTROLLER IC

Check for Samples: DRV8812

FEATURES

- **Dual-H-Bridge Current-Control Motor Driver**
  - **Capable of Driving a Bipolar Stepper or Two DC Motors**
  - **Two-Bit Winding Current Control Allows Up to Four Current Levels**
  - **Low MOSFET On-Resistance**
- **1.6-A Maximum Drive Current at 24 V, 25°C**
- **Built-In 3.3-V Reference Output**
- **Industry-Standard Parallel Digital Control Interface**
- **8-V to 45-V Operating Supply Voltage Range**
- **Thermally Enhanced HTSSOP and QFN Surface Mount Packages**

APPLICATIONS

- **Automatic Teller Machines**
- **Money Handling Machines**
- **Video Security Cameras**
- **Printers**
- **Scanners**
- **Office Automation Machines**
- **Gaming Machines**
- **Factory Automation**
- **Robotics**

DESCRIPTION

The DRV8812 provides an integrated motor driver solution for printers, scanners, and other automated equipment applications. The device has two H-bridge drivers, and can drive a bipolar stepper motor or two DC motors. The output driver block for each consists of N-channel power MOSFET's configured as full H-bridges to drive the motor windings. The DRV8812 is capable of driving up to 1.6-A of output current (with proper heatsinking, at 24 V and 25°C).

A simple parallel digital control interface is compatible with industry-standard devices. Decay mode is programmable.

Internal shutdown functions are provided for over current protection, short circuit protection, under voltage lockout and overtemperature.

The DRV8812 is available in a 28-pin HTSSOP package with PowerPAD™ and in a 28-pin QFN package PowerPAD™ (Eco-friendly: RoHS & no Sb/Br).

ORDERING INFORMATION(1)

T_A	PACKAGE(2)		ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	PowerPAD™ (HTSSOP) - PWP	Reel of 2000	DRV8812PWPR	DRV8812
	PowerPAD™ (QFN) - RHD	Reel of 3000	DRV8812RHDR	

(1) For the most current packaging and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.
(2) Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

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PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of the Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

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DEVICE INFORMATION

Functional Block Diagram

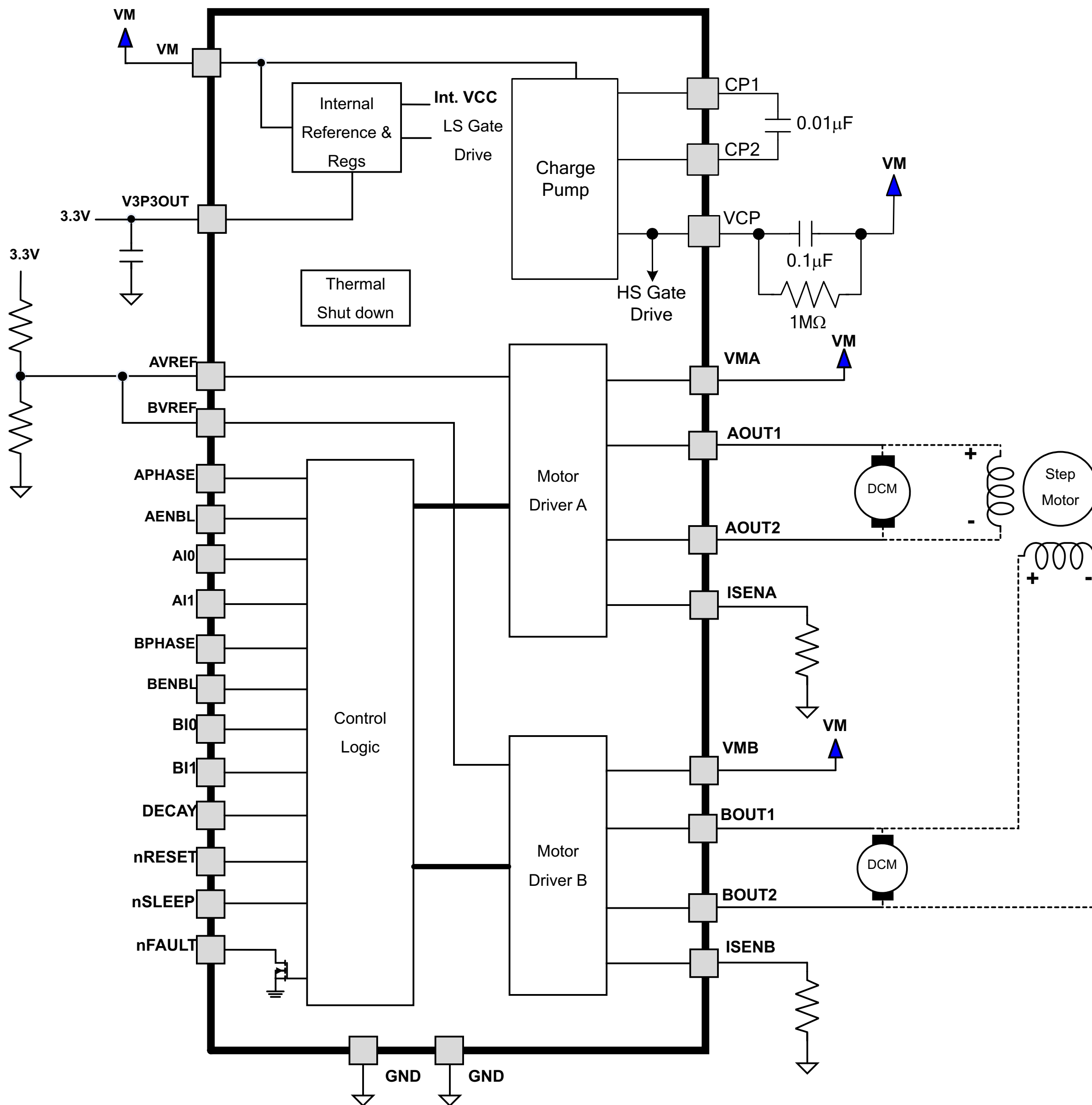

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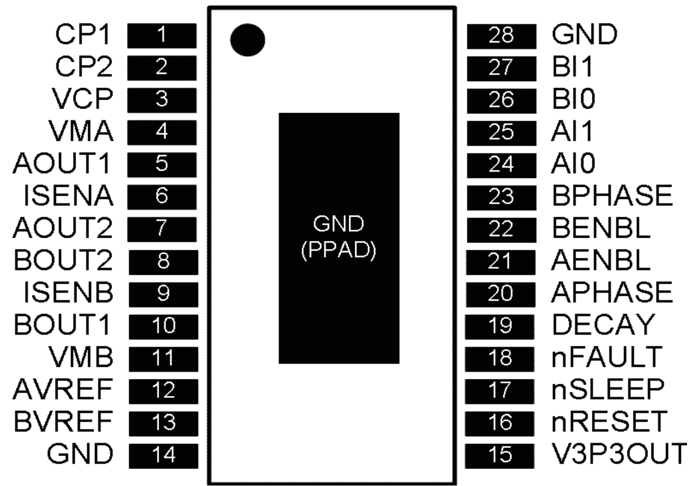
Table 1. TERMINAL FUNCTIONS

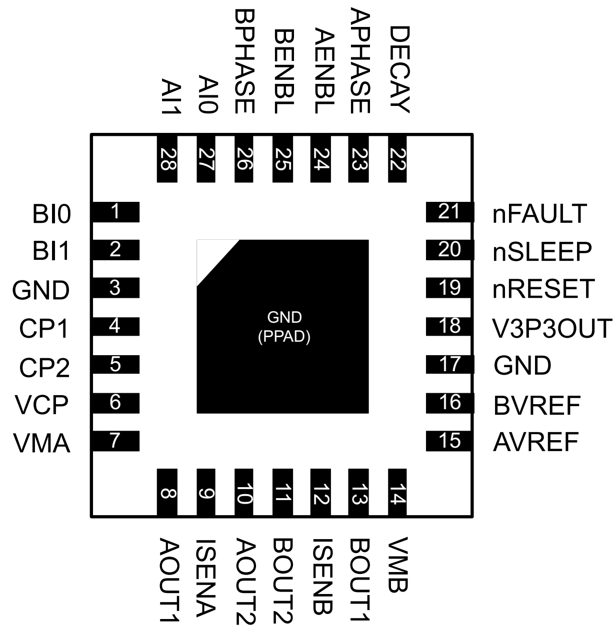
NAME	PIN		I/O(1)	DESCRIPTION	EXTERNAL COMPONENTS OR CONNECTIONS
	PWP	RHD			
POWER AND GROUND					
GND	14, 28	3, 17	-	Device ground	
VMA	4	7	-	Bridge A power supply	Connect to motor supply (8 - 45 V). Both pins must be connected to same supply.
VMB	11	14	-	Bridge B power supply	
V3P3OUT	15	18	O	3.3-V regulator output	Bypass to GND with a 0.47-μF 6.3-V ceramic capacitor. Can be used to supply VREF.
CP1	1	4	IO	Charge pump flying capacitor	Connect a 0.01-μF 50-V capacitor between CP1 and CP2.
CP2	2	5	IO	Charge pump flying capacitor	
VCP	3	6	IO	High-side gate drive voltage	Connect a 0.1-μF 16-V ceramic capacitor and a 1-MΩ resistor to VM.
CONTROL					
AENBL	21	24	I	Bridge A enable	Logic high to enable bridge A
APHASE	20	23	I	Bridge A phase (direction)	Logic high sets AOUT1 high, AOUT2 low
AI0	24	27	I	Bridge A current set	Sets bridge A current: 00 = 100%, 01 = 71%, 10 = 38%, 11 = 0
AI1	25	28	I		
BENBL	22	25	I	Bridge B enable	Logic high to enable bridge B
BPHASE	23	26	I	Bridge B phase (direction)	Logic high sets BOUT1 high, BOUT2 low
BI0	26	1	I	Bridge B current set	Sets bridge B current: 00 = 100%, 01 = 71%, 10 = 38%, 11 = 0
BI1	27	2	I		
DECAY	19	22	I	Decay mode	Low = slow decay, open = mixed decay, high = fast decay
nRESET	16	19	I	Reset input	Active-low reset input initializes internal logic and disables the H-bridge outputs
nSLEEP	17	20	I	Sleep mode input	Logic high to enable device, logic low to enter low-power sleep mode
AVREF	12	15	I	Bridge A current set reference input	Reference voltage for winding current set. Can be driven individually with an external DAC for microstepping, or tied to a reference (e.g., V3P3OUT). A 0.01-μF bypass capacitor to GND is recommended.
BVREF	13	16	I	Bridge B current set reference input	
STATUS					
nFAULT	18	21	OD	Fault	Logic low when in fault condition (overtemp, overcurrent)
OUTPUT					
ISENA	6	9	IO	Bridge A ground / Isense	Connect to current sense resistor for bridge A
ISENB	9	12	IO	Bridge B ground / Isense	Connect to current sense resistor for bridge B
AOUT1	5	8	O	Bridge A output 1	Connect to motor winding A
AOUT2	7	10	O	Bridge A output 2	
BOUT1	10	13	O	Bridge B output 1	Connect to motor winding B
BOUT2	8	11	O	Bridge B output 2	

(1) Directions: I = input, O = output, OZ = tri-state output, OD = open-drain output, IO = input/output

PWP PACKAGE
(TOP VIEW)



RHD PACKAGE
(TOP VIEW)



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ABSOLUTE MAXIMUM RATINGS

over operating free-air temperature range (unless otherwise noted) (1) (2)

		VALUE	UNIT
VMx	Power supply voltage range	–0.3 to 47	V
	Digital pin voltage range	–0.5 to 7	V
VREF	Input voltage	–0.3 to 4	V
	ISENSEx pin voltage	–0.3 to 0.8	V
	Peak motor drive output current, t < 1 μS	Internally limited	A
	Continuous motor drive output current (3)	1.6	A
	Continuous total power dissipation	See Dissipation Ratings table	
T_J	Operating virtual junction temperature range	–40 to 150	°C
T_A	Operating ambient temperature range	–40 to 85	°C
T_{stg}	Storage temperature range	–60 to 150	°C

(1) Stresses beyond those listed under absolute maximum ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under recommended operating conditions is not implied. Exposure to absolute–maximum–rated conditions for extended periods may affect device reliability.
(2) All voltage values are with respect to network ground terminal.
(3) Power dissipation and thermal limits must be observed.

THERMAL INFORMATION

THERMAL METRIC (1)		DRV8812		UNITS
		PWP	RHD	
		28 PINS	28 PINS	
θ_{JA}	Junction-to-ambient thermal resistance (2)	38.9	35.8	°C/W
θ_{JCtop}	Junction-to-case (top) thermal resistance (3)	23.3	25.1	
θ_{JB}	Junction-to-board thermal resistance (4)	21.2	8.2	
ψ_{JT}	Junction-to-top characterization parameter (5)	0.8	0.3	
ψ_{JB}	Junction-to-board characterization parameter (6)	20.9	8.2	
θ_{JCbot}	Junction-to-case (bottom) thermal resistance (7)	2.6	1.1	

(1) For more information about traditional and new thermal metrics, see the *IC Package Thermal Metrics* application report, SPRA953.
(2) The junction-to-ambient thermal resistance under natural convection is obtained in a simulation on a JEDEC-standard, high-K board, as specified in JESD51-7, in an environment described in JESD51-2a.
(3) The junction-to-case (top) thermal resistance is obtained by simulating a cold plate test on the package top. No specific JEDEC-standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.
(4) The junction-to-board thermal resistance is obtained by simulating in an environment with a ring cold plate fixture to control the PCB temperature, as described in JESD51-8.
(5) The junction-to-top characterization parameter, ψ_{JT}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA}, using a procedure described in JESD51-2a (sections 6 and 7).
(6) The junction-to-board characterization parameter, ψ_{JB}, estimates the junction temperature of a device in a real system and is extracted from the simulation data for obtaining θ_{JA} , using a procedure described in JESD51-2a (sections 6 and 7).
(7) The junction-to-case (bottom) thermal resistance is obtained by simulating a cold plate test on the exposed (power) pad. No specific JEDEC standard test exists, but a close description can be found in the ANSI SEMI standard G30-88.

RECOMMENDED OPERATING CONDITIONS

over operating free-air temperature range (unless otherwise noted)

		MIN	NOM	MAX	UNIT
V_M	Motor power supply voltage range (1)	8.2		45	V
V_{REF}	VREF input voltage (2)	1		3.5	V
I_{V3P3}	V3P3OUT load current			1	mA

(1) All V_M pins must be connected to the same supply voltage.
(2) Operational at VREF between 0 V and 1 V, but accuracy is degraded.

ELECTRICAL CHARACTERISTICS

over operating free-air temperature range (unless otherwise noted)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
POWER SUPPLIES						
I_{VM}	VM operating supply current	V_M = 24 V, f_{PWM} < 50 kHz		5	8	mA
I_{VMQ}	VM sleep mode supply current	V_M = 24 V		10	20	μA
V_{UVLO}	VM undervoltage lockout voltage	V_M rising		7.8	8.2	V
V3P3OUT REGULATOR						
V_{3P3}	V3P3OUT voltage	IOUT = 0 to 1 mA, V_M = 24 V, T_J = 25°C	3.18	3.30	3.42	V
		IOUT = 0 to 1 mA	3.10	3.30	3.50	
LOGIC-LEVEL INPUTS						
V_{IL}	Input low voltage			0.6	0.7	V
V_{IH}	Input high voltage		2		5.25	V
V_{HYS}	Input hysteresis			0.45		V
I_{IL}	Input low current	VIN = 0	–20		20	μA
I_{IH}	Input high current	VIN = 3.3 V			100	μA
nFAULT OUTPUT (OPEN-DRAIN OUTPUT)						
V_{OL}	Output low voltage	I_O = 5 mA			0.5	V
I_{OH}	Output high leakage current	V_O = 3.3 V			1	μA
DECAY INPUT						
V_{IL}	Input low threshold voltage	For slow decay mode	0		0.8	V
V_{IH}	Input high threshold voltage	For fast decay mode	2			V
I_{IN}	Input current				±40	μA
H-BRIDGE FETS						
$R_{DS(ON)}$	HS FET on resistance	V_M = 24 V, I_O = 1 A, T_J = 25°C		0.63		Ω
		V_M = 24 V, I_O = 1 A, T_J = 85°C		0.76	0.90	
$R_{DS(ON)}$	LS FET on resistance	V_M = 24 V, I_O = 1 A, T_J = 25°C		0.65		Ω
		V_M = 24 V, I_O = 1 A, T_J = 85°C		0.78	0.90	
I_{OFF}	Off-state leakage current		–20		20	μA
MOTOR DRIVER						
f_{PWM}	Internal PWM frequency			50		kHz
t_{BLANK}	Current sense blanking time			3.75		μs
t_R	Rise time	V_M = 24 V	100		360	ns
t_F	Fall time	V_M = 24 V	80		250	ns
t_{DEAD}	Dead time			400		ns
t_{DEG}	Input deglitch time		1.3		2.9	μs
PROTECTION CIRCUITS						
I_{OCP}	Overcurrent protection trip level		1.8		5	A
t_{TSD}	Thermal shutdown temperature	Die temperature	150	160	180	°C
CURRENT CONTROL						
I_{REF}	xVREF input current	xVREF = 3.3 V	–3		3	μA
V_{TRIP}	xISENSE trip voltage	xVREF = 3.3 V, 100% current setting	635	660	685	mV
		xVREF = 3.3 V, 71% current setting	445	469	492	
		xVREF = 3.3 V, 38% current setting	225	251	276	
A_{ISENSE}	Current sense amplifier gain	Reference only		5		V/V

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FUNCTIONAL DESCRIPTION

PWM Motor Drivers

The DRV8812 contains two H-bridge motor drivers with current-control PWM circuitry. A block diagram of the motor control circuitry is shown in Figure 1. A bipolar stepper motor is shown, but the drivers can also drive two separate DC motors.

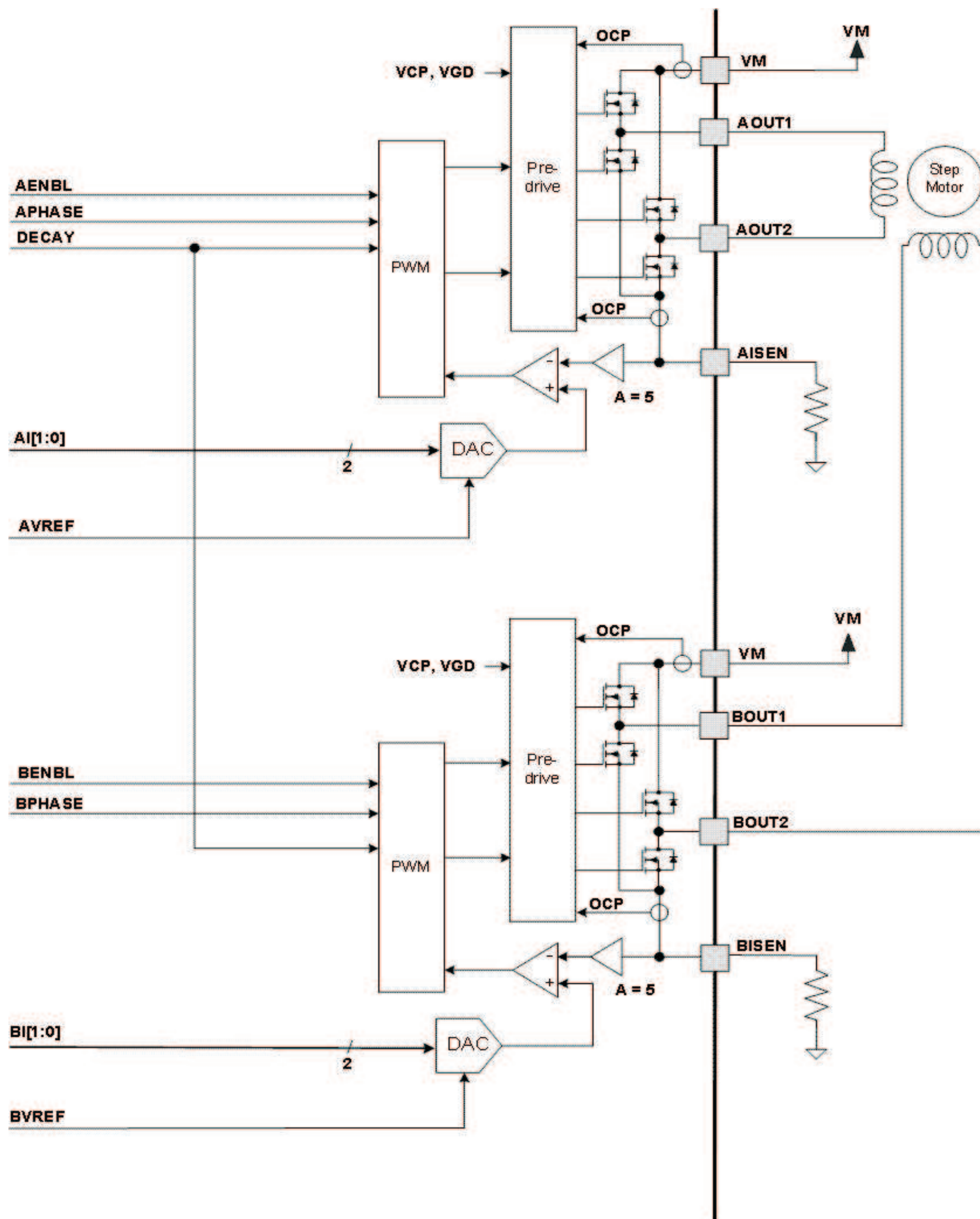

Figure 1. Motor Control Circuitry

Note that there are multiple VM motor power supply pins. All VM pins must be connected together to the motor supply voltage.

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Bridge Control

The xPHASE input pins control the direction of current flow through each H-bridge. The xENBL input pins enable the H-bridge outputs when active high. Table 2 shows the logic.

Table 2. H-Bridge Logic

xENBL	xPHASE	xOUT1	xOUT2
0	X	Z	Z
1	1	H	L
1	0	L	H

Current Regulation

The current through the motor windings is regulated by a fixed-frequency PWM current regulation, or current chopping. When an H-bridge is enabled, current rises through the winding at a rate dependent on the DC voltage and inductance of the winding. Once the current hits the current chopping threshold, the bridge disables the current until the beginning of the next PWM cycle.

For stepping motors, current regulation is normally used at all times, and can changing the current can be used to microstep the motor. For DC motors, current regulation is used to limit the start-up and stall current of the motor.

The PWM chopping current is set by a comparator which compares the voltage across a current sense resistor connected to the xISEN pins, multiplied by a factor of 5, with a reference voltage. The reference voltage is input from the xVREF pins, and is scaled by a 2-bit DAC that allows current settings of 100%, 71%, 38% of full-scale, plus zero.

The full-scale (100%) chopping current is calculated in Equation 1.

$$I_{CHOP} = \frac{V_{REFX}}{5 \bullet R_{ISENSE}} \quad (1)$$

Example:

If a 0.5-Ω sense resistor is used and the VREFx pin is 3.3 V, the full-scale (100%) chopping current will be 3.3 V / (5 x 0.5 Ω) = 1.32 A.

Two input pins per H-bridge (xI1 and xI0) are used to scale the current in each bridge as a percentage of the full-scale current set by the VREF input pin and sense resistance. The function of the pins is shown in Table 3.

Table 3. H-Bridge Pin Functions

xI1	xI0	RELATIVE CURRENT (% FULL-SCALE CHOPPING CURRENT)
1	1	0% (Bridge disabled)
1	0	38%
0	1	71%
0	0	100%

Note that when both xI bits are 1, the H-bridge is disabled and no current flows.

Example:

If a 0.5-Ω sense resistor is used and the VREF pin is 3.3 V, the chopping current will be 1.32 A at the 100% setting (xI1, xI0 = 00). At the 71% setting (xI1, xI0 = 01) the current will be 1.32 A x 0.71 = 0.937 A, and at the 38% setting (xI1, xI0 = 10) the current will be 1.32 A x 0.38 = 0.502 A. If (xI1, xI0 = 11) the bridge will be disabled and no current will flow.

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Decay Mode

During PWM current chopping, the H-bridge is enabled to drive current through the motor winding until the PWM current chopping threshold is reached. This is shown in Figure 2 as case 1. The current flow direction shown indicates the state when the xENBL pin is high.

Once the chopping current threshold is reached, the H-bridge can operate in two different states, fast decay or slow decay.

In fast decay mode, once the PWM chopping current level has been reached, the H-bridge reverses state to allow winding current to flow in a reverse direction. As the winding current approaches zero, the bridge is disabled to prevent any reverse current flow. Fast decay mode is shown in Figure 2 as case 2.

In slow decay mode, winding current is re-circulated by enabling both of the low-side FETs in the bridge. This is shown in Figure 2 as case 3.

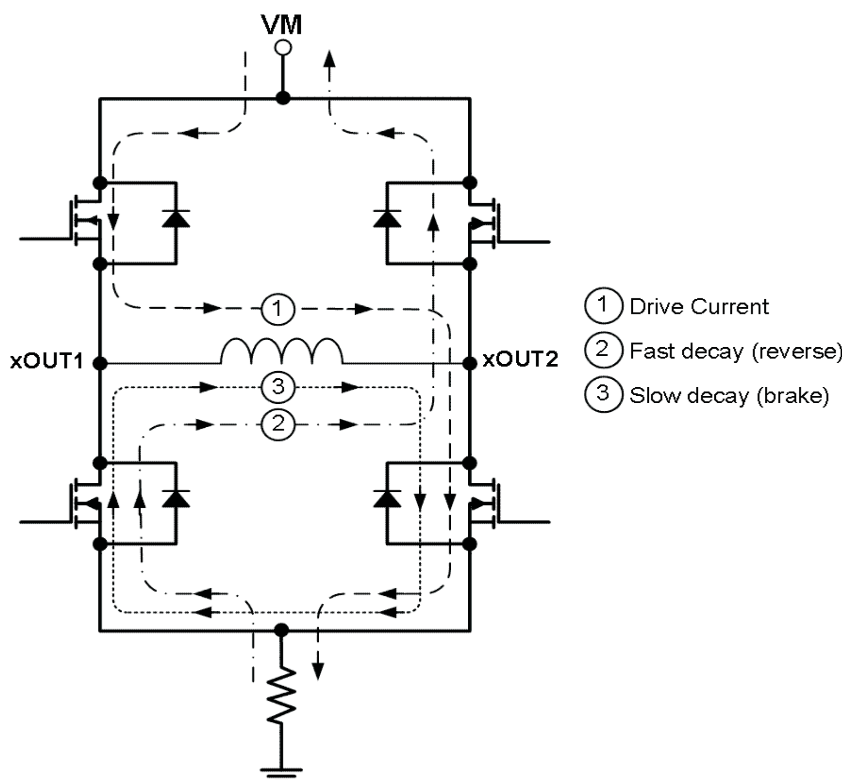

Figure 2. Decay Mode

The DRV8812 supports fast decay, slow decay and a mixed decay mode. Slow, fast, or mixed decay mode is selected by the state of the DECAY pin - logic low selects slow decay, open selects mixed decay operation, and logic high sets fast decay mode. Note that the DECAY pin sets the decay mode for both H-bridges.

Mixed decay mode begins as fast decay, but at a fixed period of time (75% of the PWM cycle) switches to slow decay mode for the remainder of the fixed PWM period.

Blanking Time

After the current is enabled in an H-bridge, the voltage on the xISEN pin is ignored for a fixed period of time before enabling the current sense circuitry. This blanking time is fixed at 3.75 μs. Note that the blanking time also sets the minimum on time of the PWM.

nRESET and nSLEEP Operation

The nRESET pin, when driven active low, resets the internal logic. It also disables the H-bridge drivers. All inputs are ignored while nRESET is active.

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Driving nSLEEP low will put the device into a low power sleep state. In this state, the H-bridges are disabled, the gate drive charge pump is stopped, the V3P3OUT regulator is disabled, and all internal clocks are stopped. In this state all inputs are ignored until nSLEEP returns inactive high. When returning from sleep mode, some time (approximately 1 ms) needs to pass before the motor driver becomes fully operational.

Protection Circuits

The DRV8812 is fully protected against undervoltage, overcurrent and overtemperature events.

Overcurrent Protection (OCP)

An analog current limit circuit on each FET limits the current through the FET by removing the gate drive. If this analog current limit persists for longer than the OCP time, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. The device will remain disabled until either nRESET pin is applied, or VM is removed and re-applied.

Overcurrent conditions on both high and low side devices; i.e., a short to ground, supply, or across the motor winding will all result in an overcurrent shutdown. Note that overcurrent protection does not use the current sense circuitry used for PWM current control, and is independent of the I_{SENSE} resistor value or VREF voltage.

Thermal Shutdown (TSD)

If the die temperature exceeds safe limits, all FETs in the H-bridge will be disabled and the nFAULT pin will be driven low. Once the die temperature has fallen to a safe level operation will automatically resume.

Undervoltage Lockout (UVLO)

If at any time the voltage on the VM pins falls below the undervoltage lockout threshold voltage, all circuitry in the device will be disabled and internal logic will be reset. Operation will resume when V_M rises above the UVLO threshold.

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THERMAL INFORMATION

Thermal Protection

The DRV8812 has thermal shutdown (TSD) as described above. If the die temperature exceeds approximately 150°C, the device will be disabled until the temperature drops to a safe level.

Any tendency of the device to enter TSD is an indication of either excessive power dissipation, insufficient heatsinking, or too high an ambient temperature.

Power Dissipation

Power dissipation in the DRV8812 is dominated by the power dissipated in the output FET resistance, or $R_{DS(ON)}$. Average power dissipation when running a stepper motor can be roughly estimated by Equation 2.

$$P_{TOT} = 4 \bullet R_{DS(ON)} \bullet (I_{OUT(RMS)})^2 \quad (2)$$

where P_{TOT} is the total power dissipation, $R_{DS(ON)}$ is the resistance of each FET, and $I_{OUT(RMS)}$ is the RMS output current being applied to each winding. $I_{OUT(RMS)}$ is equal to the approximately 0.7x the full-scale output current setting. The factor of 4 comes from the fact that there are two motor windings, and at any instant two FETs are conducting winding current for each winding (one high-side and one low-side).

The maximum amount of power that can be dissipated in the device is dependent on ambient temperature and heatsinking.

Note that $R_{DS(ON)}$ increases with temperature, so as the device heats, the power dissipation increases. This must be taken into consideration when sizing the heatsink.

Heatsinking

The PowerPAD™ package uses an exposed pad to remove heat from the device. For proper operation, this pad must be thermally connected to copper on the PCB to dissipate heat. On a multi-layer PCB with a ground plane, this can be accomplished by adding a number of vias to connect the thermal pad to the ground plane. On PCBs without internal planes, copper area can be added on either side of the PCB to dissipate heat. If the copper area is on the opposite side of the PCB from the device, thermal vias are used to transfer the heat between top and bottom layers.

For details about how to design the PCB, refer to TI application report SLMA002, " PowerPAD™ Thermally Enhanced Package" and TI application brief SLMA004, " PowerPAD™ Made Easy", available at www.ti.com.

In general, the more copper area that can be provided, the more power can be dissipated.

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead/Ball Finish	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
DRV8812PWP	ACTIVE	HTSSOP	PWP	28	50	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	DRV8812	Samples
DRV8812PWPR	ACTIVE	HTSSOP	PWP	28	2000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-1-260C-UNLIM	-40 to 85	DRV8812	Samples
DRV8812RHDR	ACTIVE	VQFN	RHD	28	3000	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	DRV8812	Samples
DRV8812RHDT	ACTIVE	VQFN	RHD	28	250	Green (RoHS & no Sb/Br)	CU NIPDAU	Level-2-260C-1 YEAR	-40 to 85	DRV8812	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) Eco Plan - The planned eco-friendly classification: Pb-Free (RoHS), Pb-Free (RoHS Exempt), or Green (RoHS & no Sb/Br) - please check http://www.ti.com/productcontent for the latest availability information and additional product content details.
TBD: The Pb-Free/Green conversion plan has not been defined.
Pb-Free (RoHS): TI's terms "Lead-Free" or "Pb-Free" mean semiconductor products that are compatible with the current RoHS requirements for all 6 substances, including the requirement that lead not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, TI Pb-Free products are suitable for use in specified lead-free processes.
Pb-Free (RoHS Exempt): This component has a RoHS exemption for either 1) lead-based flip-chip solder bumps used between the die and package, or 2) lead-based die adhesive used between the die and leadframe. The component is otherwise considered Pb-Free (RoHS compatible) as defined above.
Green (RoHS & no Sb/Br): TI defines "Green" to mean Pb-Free (RoHS compatible), and free of Bromine (Br) and Antimony (Sb) based flame retardants (Br or Sb do not exceed 0.1% by weight in homogeneous material)

(3) MSL, Peak Temp. -- The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

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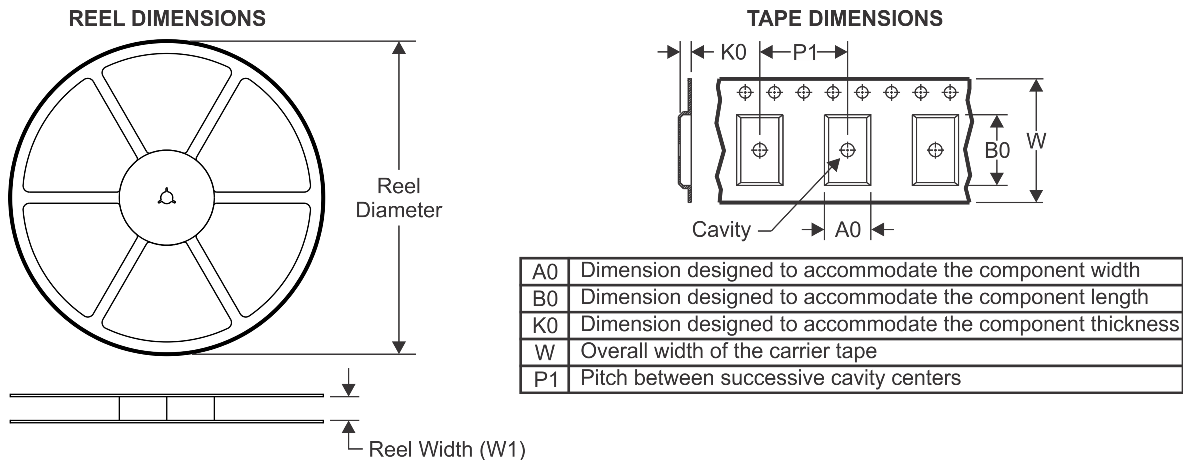
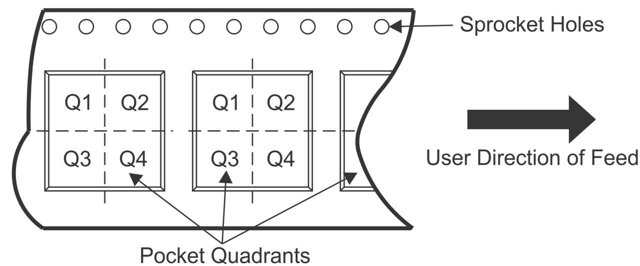
TAPE AND REEL INFORMATION



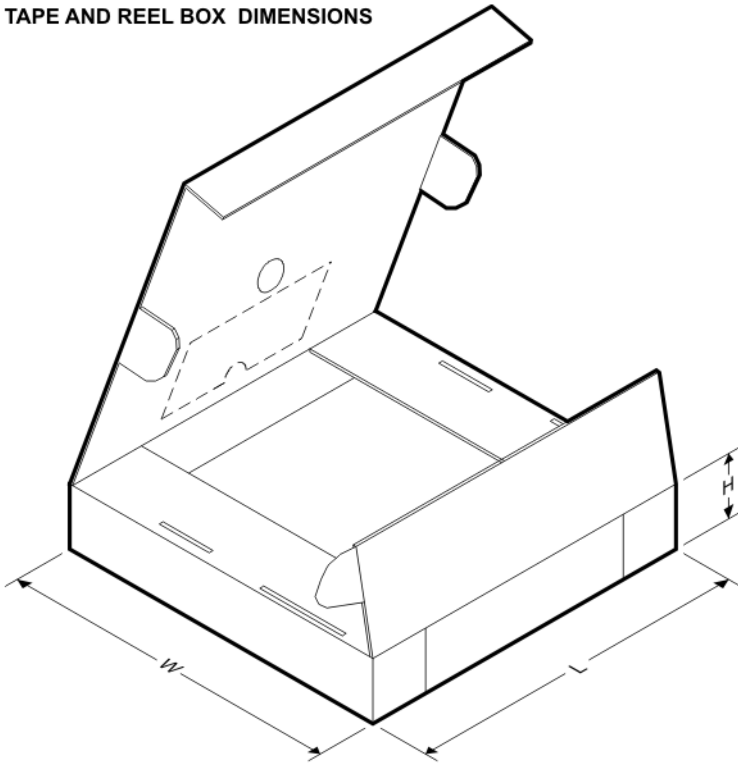
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
DRV8812PWPR	HTSSOP	PWP	28	2000	330.0	16.4	6.9	10.2	1.8	12.0	16.0	Q1
DRV8812RHDR	VQFN	RHD	28	3000	330.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2
DRV8812RHDT	VQFN	RHD	28	250	180.0	12.4	5.3	5.3	1.5	8.0	12.0	Q2

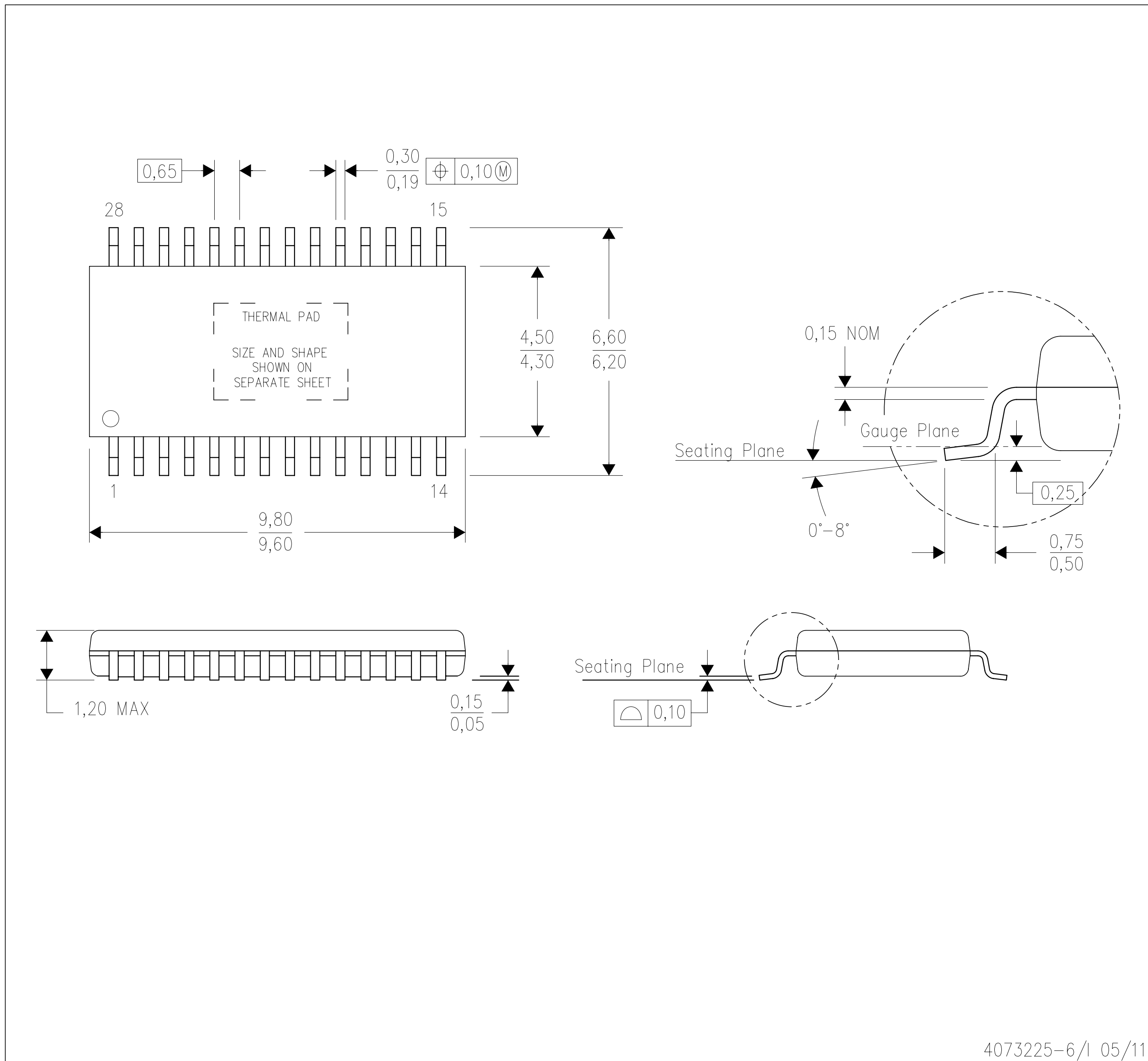
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
DRV8812PWPR	HTSSOP	PWP	28	2000	367.0	367.0	38.0
DRV8812RHDR	VQFN	RHD	28	3000	367.0	367.0	35.0
DRV8812RHDT	VQFN	RHD	28	250	210.0	185.0	35.0

PWP (R-PDSO-G28) PowerPAD™ PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in millimeters.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusions. Mold flash and protrusion shall not exceed 0.15 per side.
D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 for information regarding recommended board layout. This document is available at www.ti.com <http: //www.ti.com>.
E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
E. Falls within JEDEC MO-153

PowerPAD is a trademark of Texas Instruments.

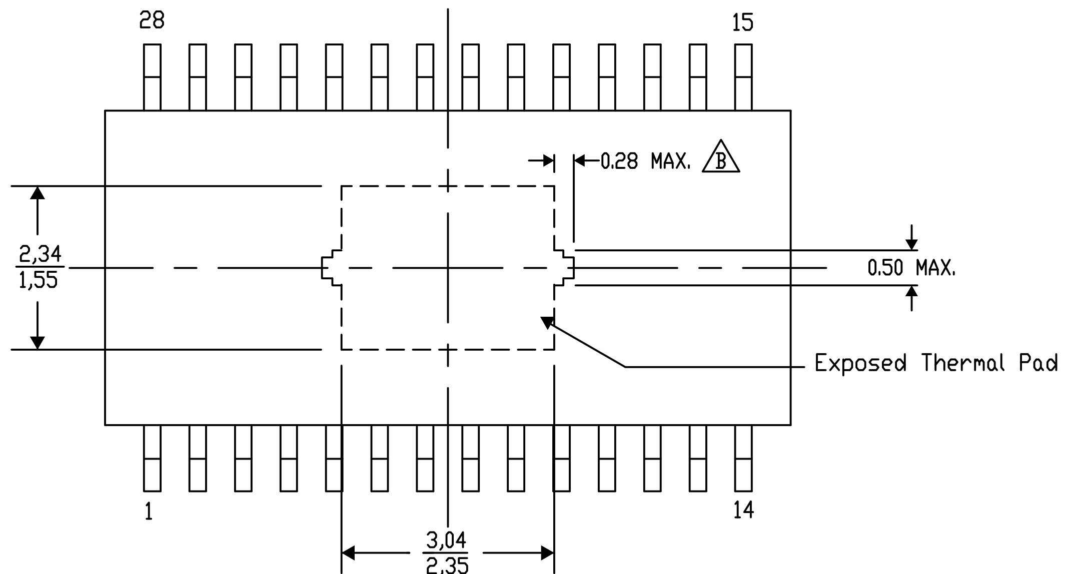
PWP (R–PDSO–G28) PowerPAD™ SMALL PLASTIC OUTLINE

THERMAL INFORMATION

This PowerPAD™ package incorporates an exposed thermal pad that is designed to be attached to a printed circuit board (PCB). The thermal pad must be soldered directly to the PCB. After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For additional information on the PowerPAD package and how to take advantage of its heat dissipating abilities, refer to Technical Brief, PowerPAD Thermally Enhanced Package, Texas Instruments Literature No. SLMA002 and Application Brief, PowerPAD Made Easy, Texas Instruments Literature No. SLMA004. Both documents are available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



Top View

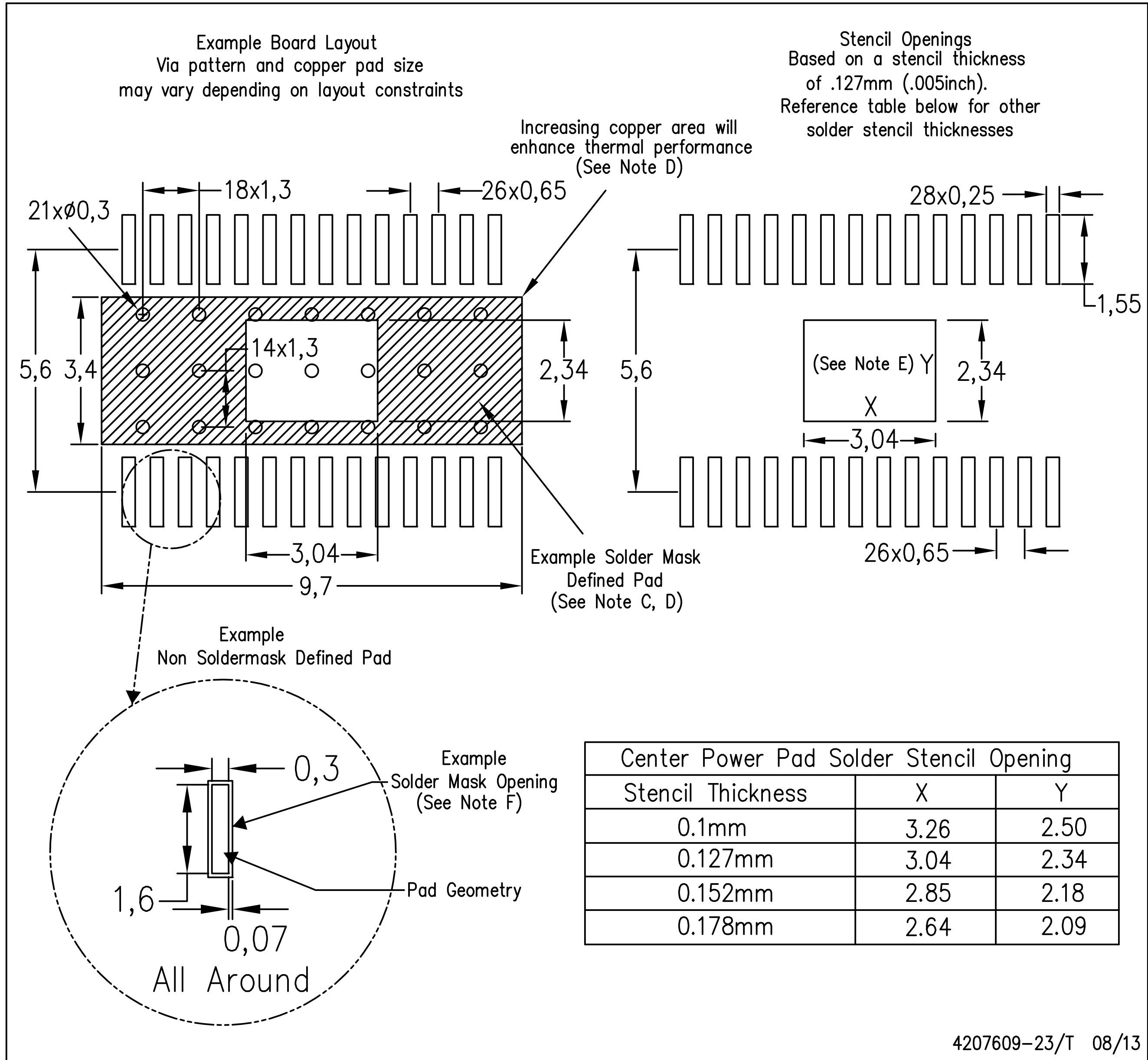
Exposed Thermal Pad Dimensions

4206332–39/AF 06/13

NOTE: A. All linear dimensions are in millimeters
B. Exposed tie strap features may not be present.

PowerPAD is a trademark of Texas Instruments

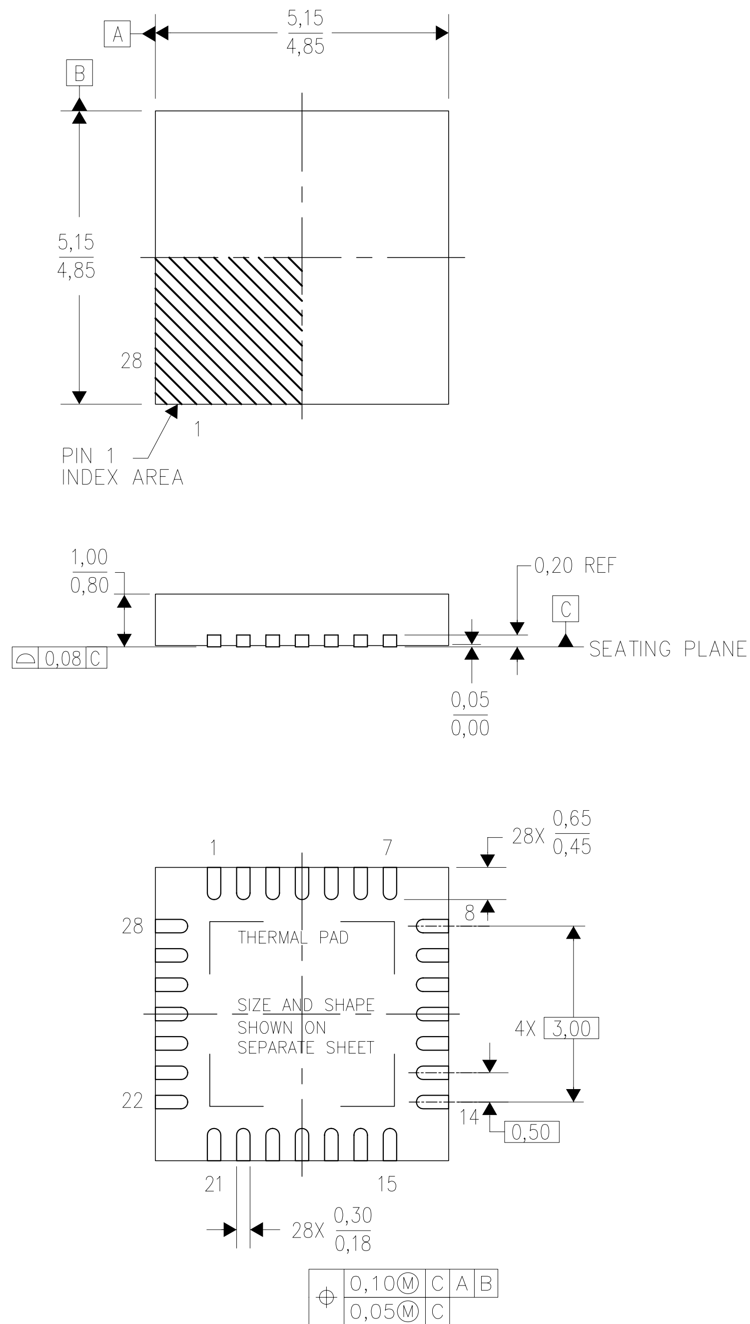
PWP (R-PDSO-G28) PowerPAD™ PLASTIC SMALL OUTLINE



Center Power Pad Solder Stencil Opening		
Stencil Thickness	X	Y
0.1mm	3.26	2.50
0.127mm	3.04	2.34
0.152mm	2.85	2.18
0.178mm	2.64	2.09

NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Customers should place a note on the circuit board fabrication drawing not to alter the center solder mask defined pad.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Technical Brief, PowerPad Thermally Enhanced Package, Texas Instruments Literature No. SLMA002, SLMA004, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http: //www.ti.com>. Publication IPC-7351 is recommended for alternate designs.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Example stencil design based on a 50% volumetric metal load solder paste. Refer to IPC-7525 for other stencil recommendations.
- F. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.

RHD (S-PVQFN-N28) PLASTIC QUAD FLATPACK NO-LEAD



4204400/F 09/11

NOTES:
- A. All linear dimensions are in millimeters. Dimensioning and tolerancing per ASME Y14.5M—1994.
- B. This drawing is subject to change without notice.
- C. QFN (Quad Flatpack No—Lead) Package configuration.
- D. The package thermal pad must be soldered to the board for thermal and mechanical performance.
- E. See the additional figure in the Product Data Sheet for details regarding the exposed thermal pad features and dimensions.
- F. Falls within JEDEC MO—220.

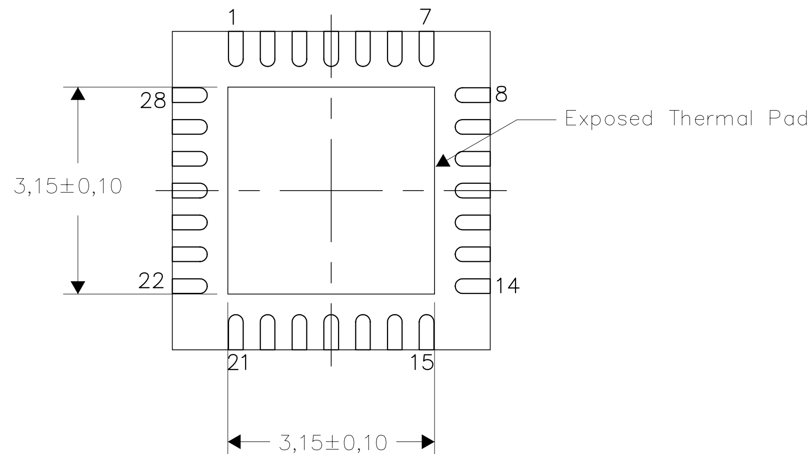
RHD (S-PVQFN-N28) PLASTIC QUAD FLATPACK NO-LEAD

THERMAL INFORMATION

This package incorporates an exposed thermal pad that is designed to be attached directly to an external heatsink. The thermal pad must be soldered directly to the printed circuit board (PCB). After soldering, the PCB can be used as a heatsink. In addition, through the use of thermal vias, the thermal pad can be attached directly to the appropriate copper plane shown in the electrical schematic for the device, or alternatively, can be attached to a special heatsink structure designed into the PCB. This design optimizes the heat transfer from the integrated circuit (IC).

For information on the Quad Flatpack No-Lead (QFN) package and its advantages, refer to Application Report, QFN/SON PCB Attachment, Texas Instruments Literature No. SLUA271. This document is available at www.ti.com.

The exposed thermal pad dimensions for this package are shown in the following illustration.



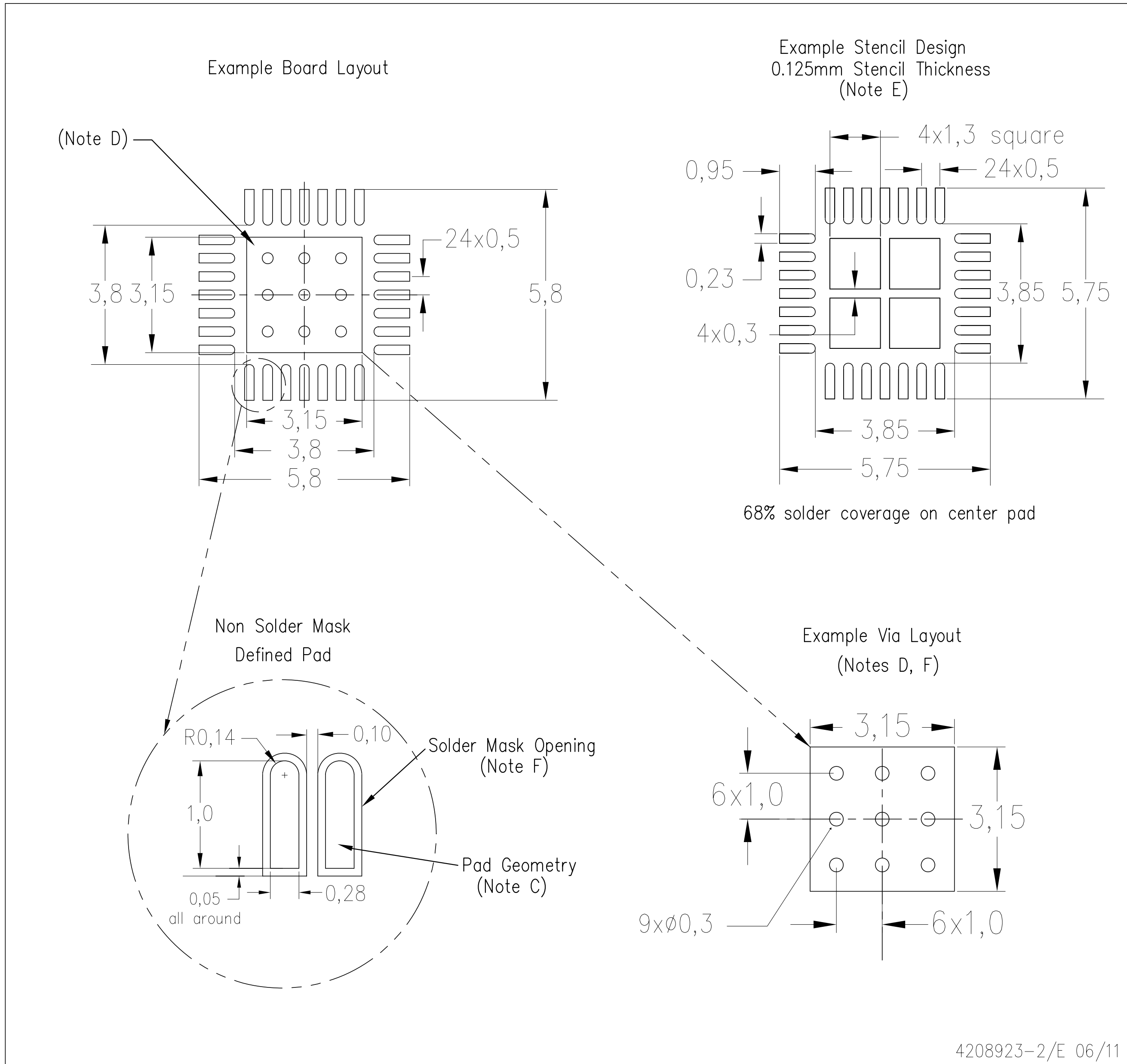
Bottom View

Exposed Thermal Pad Dimensions

4206358-2/I 05/11

NOTE: All linear dimensions are in millimeters

RHD (S-PVQFN-N28) PLASTIC QUAD FLATPACK NO-LEAD



NOTES:
- A. All linear dimensions are in millimeters.
- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. This package is designed to be soldered to a thermal pad on the board. Refer to Application Note, Quad Flat-Pack Packages, Texas Instruments Literature No. SLUA271, and also the Product Data Sheets for specific thermal information, via requirements, and recommended board layout. These documents are available at www.ti.com <http: //www.ti.com>.
- E. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC 7525 for stencil design considerations.
- F. Customers should contact their board fabrication site for recommended solder mask tolerances and via tenting recommendations for vias placed in thermal pad.

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